



60

N-Channel 60 V (D-S) Super Junction MOSFET

127nC

305

$\begin{array}{|c|c|c|c|c|} \hline \textbf{PRODUCT SUMMARY} \\ \hline V_{DS}\left(V\right) & R_{DS(on)}\left(m\Omega\right) (\mathsf{Typ.}) & I_{D}\left(A\right)^{a} & Q_{g}\left(\mathsf{Typ.}\right) \\ \hline \end{array}$

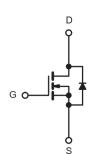
0.8at V_{GS} = 10 V

FEATURES

- DT-SJ Power MOSFET
- 100 % Rg and UIS Tested
- Low On-Resistance

APPLICATIONS

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers



N-Channel MOSFET

		garation		
Top View	Bottom View	Top View		
		S [1 ● S [2 S [3	8] D 7] D 6] D	
PIN1	1,1	G [4	5 D	

DFN5X6-8L Pin Configuration

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V_{GS}	± 20]	
Continuous Drain Current (T _{.I} = 150 °C) ^a	T _C = 25 °C	i_	305		
Continuous Diain Current (1) = 150 C)	T _C = 100 °C	I _D	200	A	
Pulsed Drain Current ^b		I _{DM}	900		
Single Pulse Avalanche Energy		E _{AS}	545	mJ	
Maximum Power Dissipation ^c	T _C = 25 °C	P_{D}	265	W	
Maximum Fower Dissipation	T _C = 100 °C	' D	106		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to +150	°C	
Soldering Recommendations (Peak Temperature)		260]		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^d	t ≤ 10 s	R _{thJA}	-	50	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	-	0.47	0, , ,

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER SYMBOL		TEST CONDITIONS MIN.		TYP.	MAX.	UNIT	
Static				<u>'</u>			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$ - $V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$ -		-	1	μА	
Zero Gate Voltage Drain Current	DSS			-	100		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	305	-	-	Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$	-	0.8	0.96	mΩ	
Forward Transconductance a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_D = 50 \text{ A}$	-	63	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	7370	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{MHz}$	-	3230	-		
Reverse Transfer Capacitance	C _{rss}		-	160	-		
Total Gate Charge ^c	Qg		-	127	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$	-	22.6	-		
Gate-Drain Charge ^c	Q _{gd}		-	28	-		
Gate Resistance	R _g	f = 1 MHz	-	2.8	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	23	-		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, R_q = 3 \Omega$	-	18	-	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D = 50 \text{ A}, V_{GEN} = 10 \text{ V},$	-	75	-		
Fall Time ^c	t _f		-	24	-		
Drain-Source Body Diode Ratings at	nd Characteris	stics ^b (T _C = 25 °C)					
Continuous Source Current	Is	T _C = 25 °C	-	-	305	Α	
Pulsed Source Current	I _{SM}		-	-	300	Α	
Forward Voltage ^a	V _{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1.2	V	
Reverse Recovery Time	t _{rr}	L = 50 A di/dt = 100 A/vs	-	45	-	ns	
Reverse Recovery Charge	Q _{rr}	$I_F = 50 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	180	-	nC	

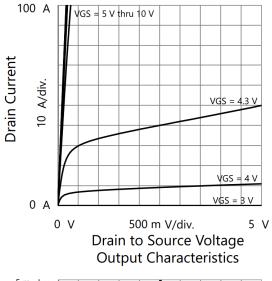
Notes

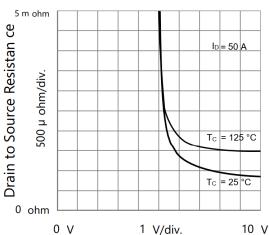
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

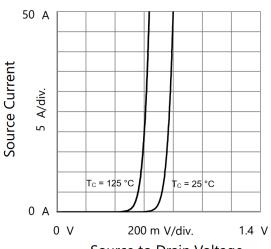


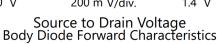
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

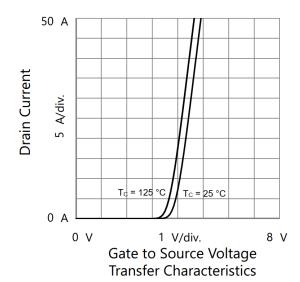


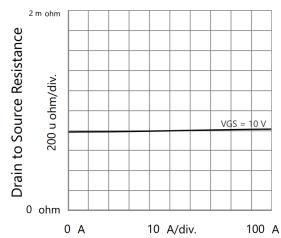


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

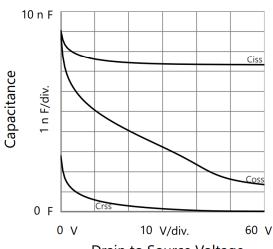








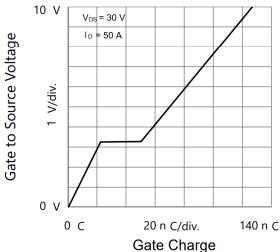
Drain Current
Drain to Source Resistance vs. Drain Current



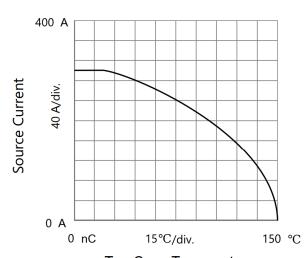
Drain to Source Voltage Capacitances



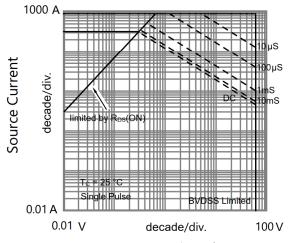
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



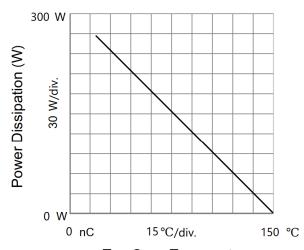
Gate Charge
Gate to Source Voltage vs. GateCharge



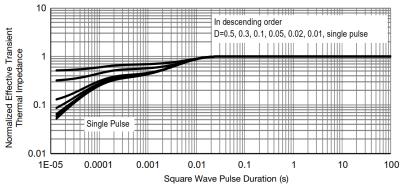
 $T_{C} \textbf{ - Case Temperature} \\ \text{ Current Derating}$



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



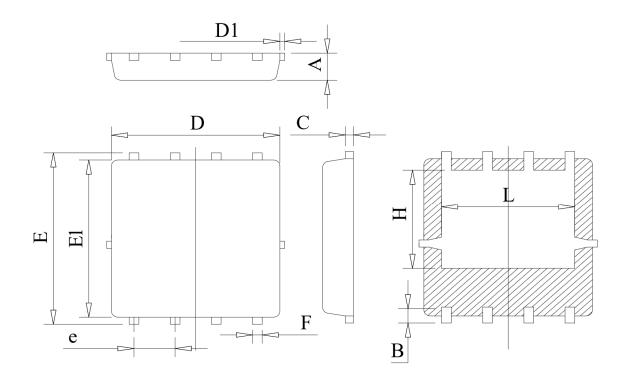
 $T_{C} \textbf{-} \textbf{Case Temperature}_{\text{Current Derating}}$



Normalized Thermal Transient Impedance, Junction-to-Case



DFN5*6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
C	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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